



DXT3904

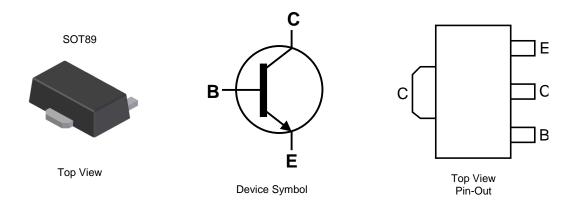
#### **40V NPN SMALL SIGNAL TRANSISTOR IN SOT89**

#### **Features**

- BV<sub>CEO</sub> > 40V
- Epitaxial Planar Die Construction
- Complementary PNP Type Available (DXT3906)
- Ideal for Medium Power Switching or Amplification Applications
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

- Case: SOT89
- Case Material: Molded Plastic, "Green" Molding Compound.
  UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208@3
- Weight: 0.072 grams (Approximate)



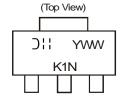
#### Ordering Information (Note 4)

Part Number	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DXT3904-13	AEC-Q101	K1N	13	12	2,500

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.
- 3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

### **Marking Information**



K1N = Product Type Marking Code YWW = Date Code Marking Y = Last Digit of Year ex: 4 = 2014 WW = Week Code 01 - 52



## Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	60	V
Collector-Emitter Voltage	V <sub>CEO</sub>	40	V
Emitter-Base Voltage	V <sub>EBO</sub>	6	V
Collector Current – Continuous	Ic	200	mA

## Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 5)	D-	0.75	· W	
Power Dissipation	(Note 6)	P <sub>D</sub>	1.2		
Thermal Resistance, Junction to Ambient Air	(Note 5)	D	166	°C/W	
Thermal Resistance, Junction to Ambient Air	(Note 6)	$R_{\theta JA}$	104	· C/VV	
Operating and Storage Temperature Range		T <sub>j</sub> , T <sub>STG</sub>	-55 to +150	°C	

## ESD Ratings (Note 7)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

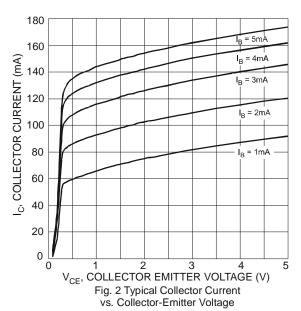
- 5. For a device mounted with the exposed collector pad on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
  6. Same as note (5), except the device is mounted with the exposed collector pad on 25mm x 25mm 1oz copper.
- 7. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

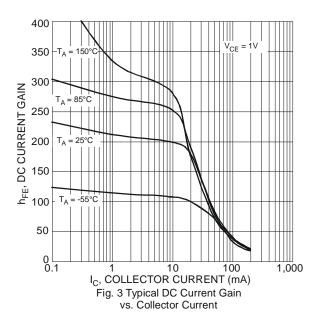


## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

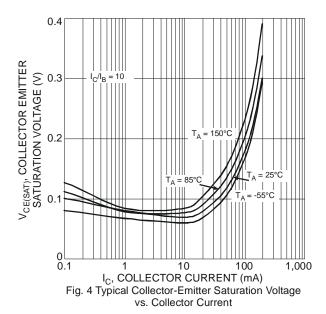
Characteristic	Symbol	Min	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)						
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	60	_	V	$I_C = 10\mu A, I_E = 0$	
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	40	_	V	$I_C = 1.0 \text{mA}, I_B = 0$	
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	6.0	_	V	$I_E = 10\mu A, I_C = 0$	
Collector Cutoff Current	I <sub>CEX</sub>	_	50	nA	$V_{CE} = 30V, V_{EB(OFF)} = 3.0V$	
Base Cutoff Current	I <sub>BL</sub>	_	50	nA	$V_{CE} = 30V, V_{EB(OFF)} = 3.0V$	
ON CHARACTERISTICS (Note 7)						
DC Current Gain	h <sub>FE</sub>	40 70 100 60 30	300 — —	_	$\begin{split} I_C &= 100 \mu A, \ V_{CE} = 1.0 V \\ I_C &= 1.0 mA, \ V_{CE} = 1.0 V \\ I_C &= 10 mA, \ V_{CE} = 1.0 V \\ I_C &= 50 mA, \ V_{CE} = 1.0 V \\ I_C &= 100 mA, \ V_{CE} = 1.0 V \end{split}$	
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	_	0.20 0.30	V	I <sub>C</sub> = 10mA, I <sub>B</sub> = 1.0mA I <sub>C</sub> = 50mA, I <sub>B</sub> = 5.0mA	
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>	0.65	0.85 0.95	V	$I_C = 10$ mA, $I_B = 1.0$ mA $I_C = 50$ mA, $I_B = 5.0$ mA	
SMALL SIGNAL CHARACTERISTICS						
Output Capacitance	C <sub>obo</sub>	_	4.0	pF	$V_{CB} = 5.0V$ , $f = 1.0MHz$ , $I_E = 0$	
Input Capacitance	$C_{ibo}$	_	8.0	pF	$V_{EB} = 0.5V$ , $f = 1.0MHz$ , $I_C = 0$	
Input Impedance	h <sub>ie</sub>	1.0	10	kΩ		
Voltage Feedback Ratio	h <sub>re</sub>	0.5	8.0	x 10 <sup>-4</sup>	V <sub>CE</sub> = 10V, I <sub>C</sub> = 1.0mA, f = 1.0kHz	
Small Signal Current Gain	h <sub>fe</sub>	100	400	_	VCE = 10V, IC = 1.0IIIA, I = 1.0KIIZ	
Output Admittance	h <sub>oe</sub>	1.0	40	μS		
Current Gain-Bandwidth Product	f <sub>T</sub>	300	_	MHz	$V_{CE} = 20V, I_{C} = 10mA, f = 100MHz$	
Noise Figure	NF	_	5.0	dB	$\begin{split} V_{CE} &= 5.0 V, \ I_C = 100 \mu A, \\ R_S &= 1.0 k \Omega, \ f = 1.0 k Hz \end{split}$	
SWITCHING CHARACTERISTICS						
Delay Time	t <sub>d</sub>		35	ns	$V_{CC} = 3.0V, I_{C} = 10mA,$	
Rise Time	t <sub>r</sub>	_	35	ns	$V_{BE(off)} = -0.5V, I_{B1} = 1.0mA$	
Storage Time	ts	_	200	ns	$V_{CC} = 3.0V, I_{C} = 10mA,$	
Fall Time	t <sub>f</sub>		50	ns	$I_{B1} = -I_{B2} = 1.0 \text{mA}$	

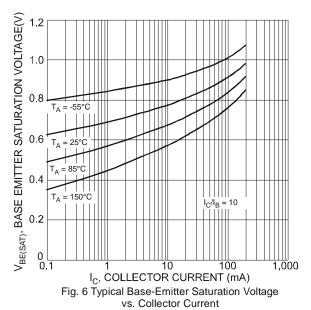
Notes: 7. Measured under pulsed condition. Pulse width =  $300\mu$ s. Duty cycle  $\leq 2\%$ .

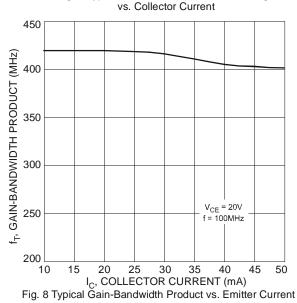


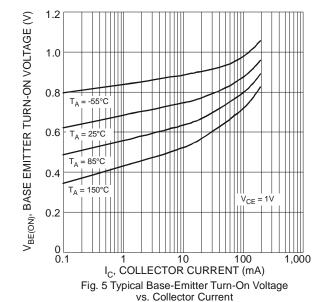












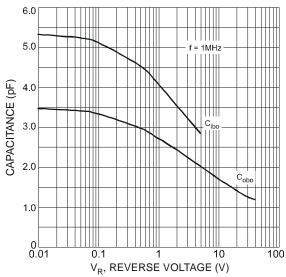
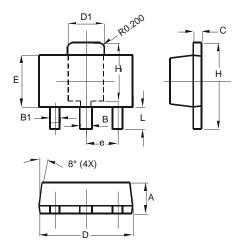


Fig. 7 Typical Capacitance Characteristics



## **Package Outline Dimensions**

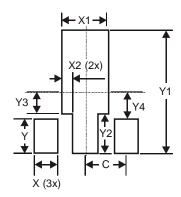
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT89				
Dim	Min	Max		
Α	1.40	1.60		
В	0.44	0.62		
B1	0.35	0.54		
C	0.35	0.44		
D	4.40	4.60		
D1	1.62	1.83		
Е	2.29	2.60		
е	1.50 Typ			
Н	3.94	4.25		
H1	2.63	2.93		
L	0.89	1.20		
All Dimensions in mm				

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
X	0.900		
X1	1.733		
X2	0.416		
Y	1.300		
Y1	4.600		
Y2	1.475		
Y3	0.950		
Y4	1.125		
С	1.500		



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